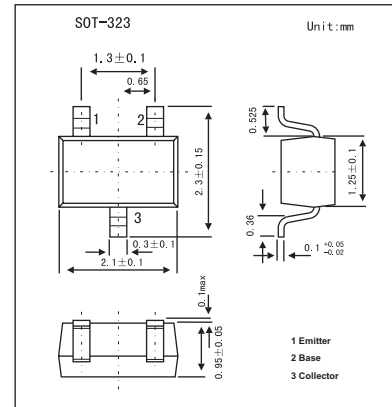


## PNP General Purpose Transistor

### 2PA1576

#### ■ Features

- Low current (max. 100 mA)
- Low voltage (max. 40 V).
- Low collector capacitance (typ. 2.5 pF).



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-40	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-100	mA
Peak collector current	I <sub>CM</sub>	-200	mA
Peak base current	I <sub>BM</sub>	-200	mA
Total power dissipation	P <sub>tot</sub>	200	mW
Storage temperature	T <sub>stg</sub>	-65 to +150	°C
Junction temperature	T <sub>j</sub>	150	°C
Operating ambient temperature	T <sub>amb</sub>	-65 to +150	°C
thermal resistance from junction to ambient	R <sub>th j-a</sub>	625	K/W

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	I <sub>E</sub> = 0; V <sub>CB</sub> = -30 V			-100	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = -30 V; T <sub>j</sub> = 150 °C			-5	μA
Emitter cut-off current	I <sub>EBO</sub>	I <sub>C</sub> = 0; V <sub>EB</sub> = -4 V			-100	nA
DC current gain	h <sub>FE</sub>	I <sub>C</sub> = -1 mA; V <sub>CE</sub> = -6 V	120		270	
2PA1576Q						
2PA1576R						
2PA1576S			270		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -50 mA; I <sub>B</sub> = -5 mA; *			-500	mV
Collector capacitance	C <sub>c</sub>	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = -12 V; f = 1 MHz		2.5	3.5	pF
Transition frequency	f <sub>T</sub>	I <sub>C</sub> = -2 mA; V <sub>CE</sub> = -12 V; f = 100 MHz	100			MHz

\* Pulse test: t<sub>p</sub> ≤ 300 μs; δ ≤ 0.02.

#### ■ hFE Classification

TYPE	2PA1576Q	2PA1576R	2PA1576S
Marking	FQ	FR	FS